


**Description**

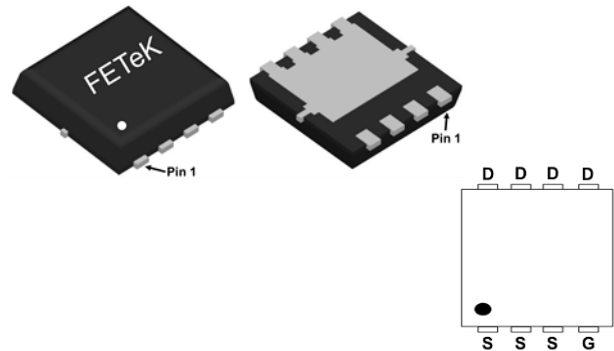
- Advanced Trench MOS Technology
- Low Gate Charge
- Low  $R_{DS(ON)}$
- 100% EAS Guaranteed
- Green Device Available

**Product Summary**

BVDSS	RDSON	ID
30V	8.0mΩ	28A

**Applications**

- Power Management in Desktop Computer or DC/DC Converters.
- Isolated DC/DC Converters in Telecom and Industrial.

**PRPAK3X3 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	±20	V
$I_D @ T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	28	A
$I_D @ T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	20	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	100	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	39.2	mJ
$I_{AS}$	Avalanche Current	28	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	21	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	65	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	6	°C/W



**N-Channel Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =12A	---	6.0	8	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =12A	---	9.4	11	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.7	2.2	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =12A	---	55	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	0.8	1.7	2.6	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =12A	---	7.1	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.2	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.1	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V , R <sub>G</sub> =3Ω I <sub>D</sub> =12A	---	7	---	ns
T <sub>r</sub>	Rise Time		---	18.8	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	19.5	---	
T <sub>f</sub>	Fall Time		---	3.4	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz	---	693	---	pF
C <sub>oss</sub>	Output Capacitance		---	332	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	34	---	

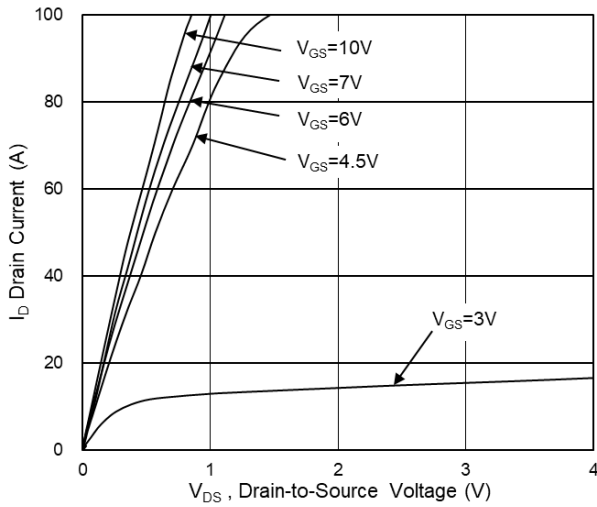
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	12	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C	---	---	1	V

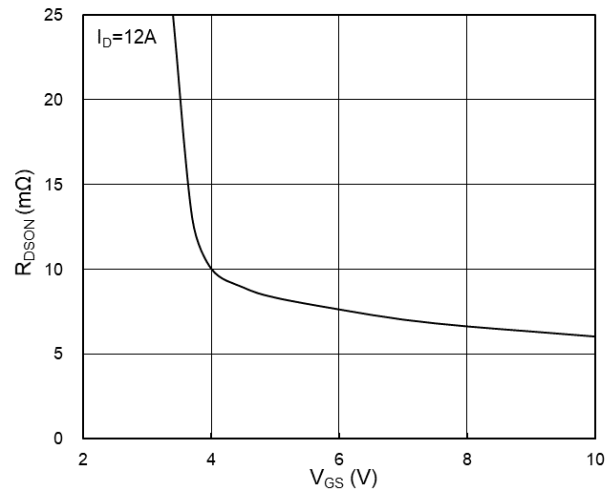
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=28A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

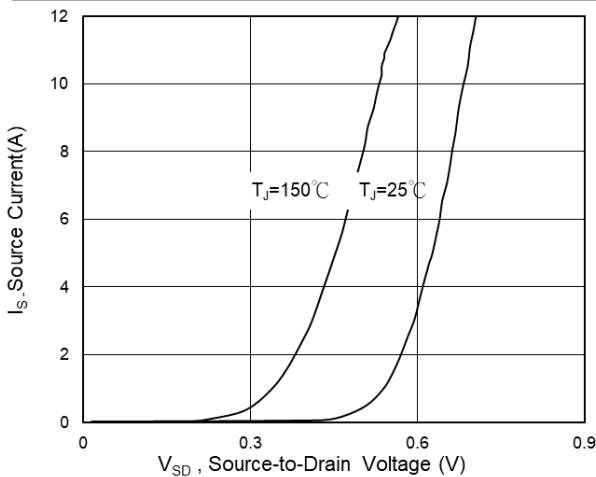
**Typical Characteristics**



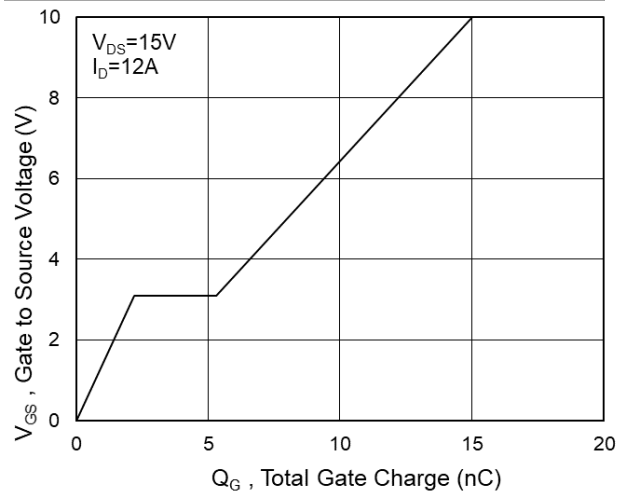
**Fig.1 Typical Output Characteristics**



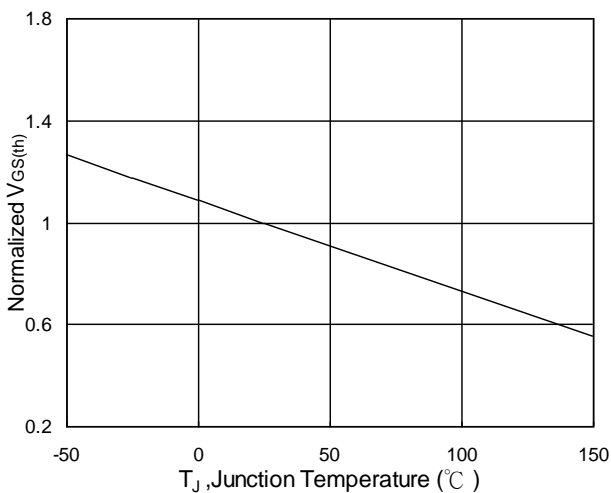
**Fig.2 On-Resistance vs G-S Voltage**



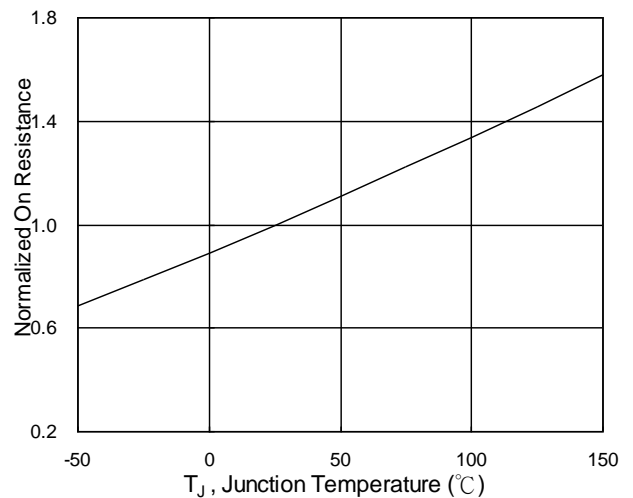
**Fig.3 Source Drain Forward Characteristics**



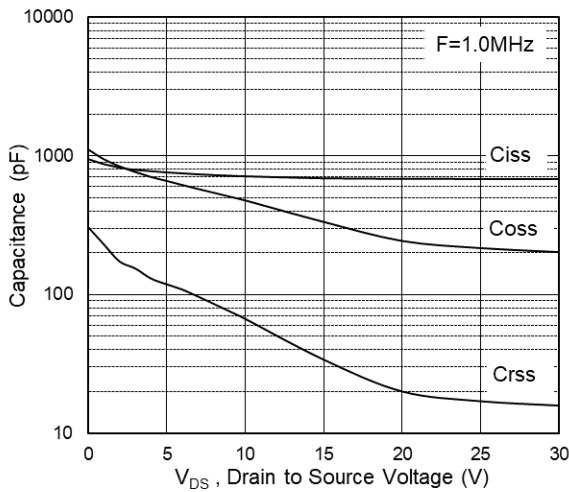
**Fig.4 Gate-Charge Characteristics**



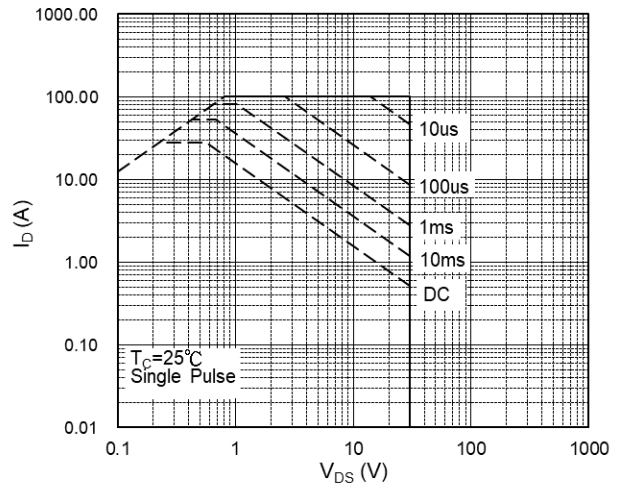
**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



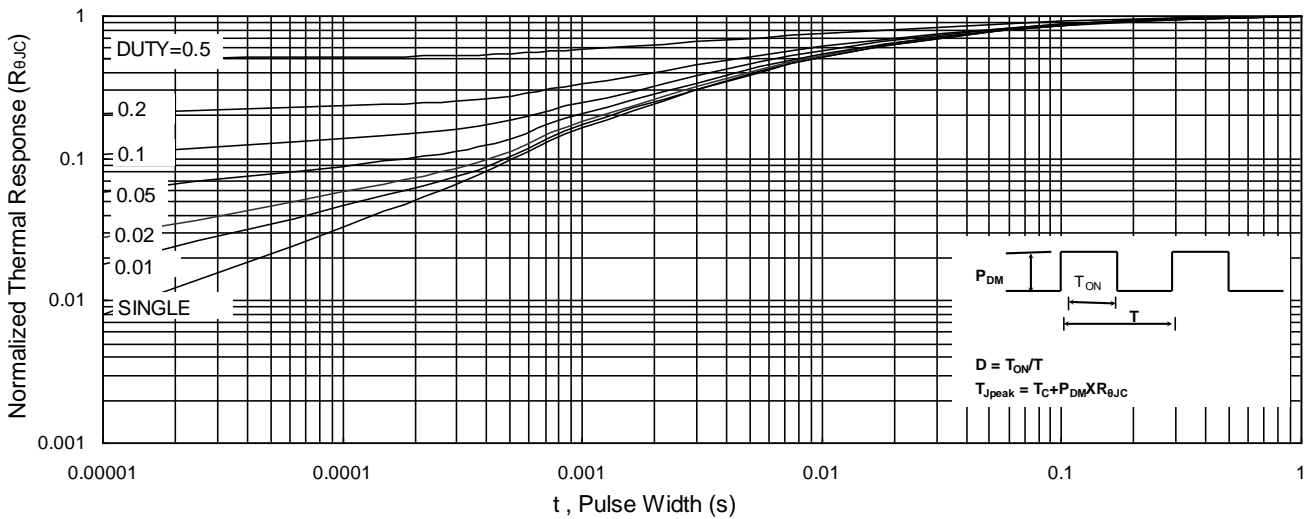
**Fig.6 Normalized  $R_{DSON}$  vs  $T_J$**



**Fig.7 Capacitance**



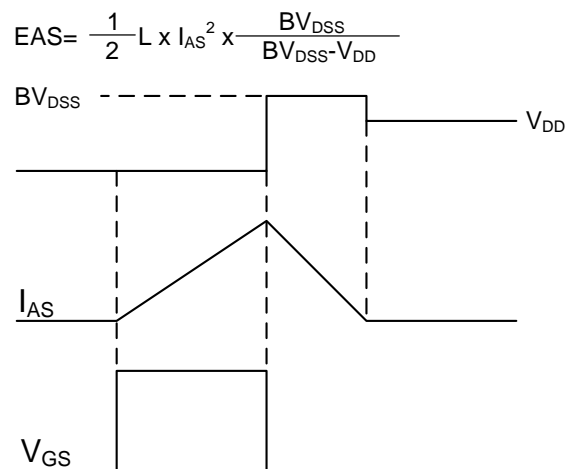
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**